

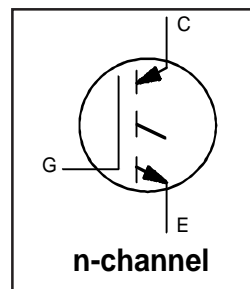
IRG4BC30S-SPbF

INSULATED GATE BIPOLAR TRANSISTOR

Standard Speed IGBT

Features

- Standard: optimized for minimum saturation voltage and low operating frequencies (< 1kHz)
- Generation 4 IGBT design provides tight parameter distribution and high efficiency
- Lead-Free



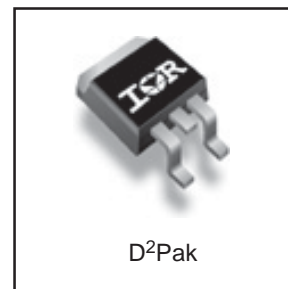
$$V_{CES} = 600V$$

$$V_{CE(on) \text{ typ.}} = 1.4V$$

$$@V_{GE} = 15V, I_C = 18A$$

Benefits

- Generation 4 IGBTs offer highest efficiency available
- IGBTs optimized for specified application conditions



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Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	34	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	18	
I_{CM}	Pulsed Collector Current ①	68	
I_{LM}	Clamped Inductive Load Current ②	68	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	10	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	100	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	42	
T_J	Operating Junction and	-55 to +150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.2	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	40	
Wt	Weight	1.44	—	g (oz)

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V _{GE} = 0V, I _C = 250μA
V _{(BR)ECS}	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	V _{GE} = 0V, I _C = 1.0A
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	0.75	—	V/°C	V _{GE} = 0V, I _C = 1.0mA
V _{CE(ON)}	Collector-to-Emitter Saturation Voltage	—	1.40	1.6	V	I _C = 18A
		—	1.84	—		I _C = 34A
		—	1.45	—		I _C = 18A, T _J = 150°C
V _{GE(th)}	Gate Threshold Voltage	3.0	—	6.0		V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)} /ΔT _J	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	V _{CE} = V _{GE} , I _C = 250μA
g _{fe}	Forward Transconductance ⑤	6.0	11	—	S	V _{CE} = 100V, I _C = 18A
I _{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	V _{GE} = 0V, V _{CE} = 600V
		—	—	2.0		V _{GE} = 0V, V _{CE} = 10V, T _J = 25°C
		—	—	1000		V _{GE} = 0V, V _{CE} = 600V, T _J = 150°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	50	75	nC	I _C = 18A
Q _{ge}	Gate - Emitter Charge (turn-on)	—	7.3	11		V _{CC} = 400V
Q _{gc}	Gate - Collector Charge (turn-on)	—	17	26		V _{GE} = 15V
t _{d(on)}	Turn-On Delay Time	—	22	—	ns	T _J = 25°C
t _r	Rise Time	—	18	—		I _C = 18A, V _{CC} = 480V
t _{d(off)}	Turn-Off Delay Time	—	540	810		V _{GE} = 15V, R _G = 23Ω
t _f	Fall Time	—	390	590		Energy losses include "tail"
E _{on}	Turn-On Switching Loss	—	0.26	—	mJ	See Fig. 9, 10, 14
E _{off}	Turn-Off Switching Loss	—	3.45	—		
E _{ts}	Total Switching Loss	—	3.71	5.6		
t _{d(on)}	Turn-On Delay Time	—	21	—	ns	T _J = 150°C,
t _r	Rise Time	—	19	—		I _C = 18A, V _{CC} = 480V
t _{d(off)}	Turn-Off Delay Time	—	790	—		V _{GE} = 15V, R _G = 23Ω
t _f	Fall Time	—	760	—		Energy losses include "tail"
E _{ts}	Total Switching Loss	—	6.55	—	mJ	See Fig. 11, 14
L _E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C _{ies}	Input Capacitance	—	1100	—	pF	V _{GE} = 0V
C _{oes}	Output Capacitance	—	72	—		V _{CC} = 30V
C _{res}	Reverse Transfer Capacitance	—	13	—		f = 1.0MHz

Notes:

- ① Repetitive rating; V_{GE} = 20V, pulse width limited by max. junction temperature (See fig. 13b).
- ② V_{CC} = 80%(V_{CES}), V_{GE} = 20V, L = 10μH, R_G = 23Ω, (See fig. 13a).
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width ≤ 80μs; duty factor ≤ 0.1%.
- ⑤ Pulse width 5.0μs, single shot.

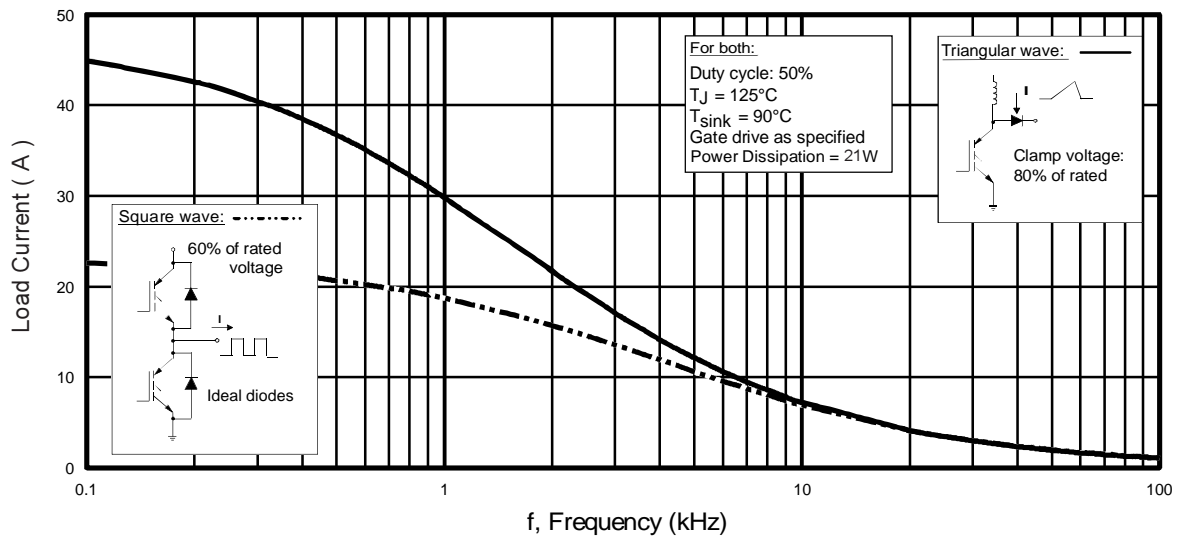


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

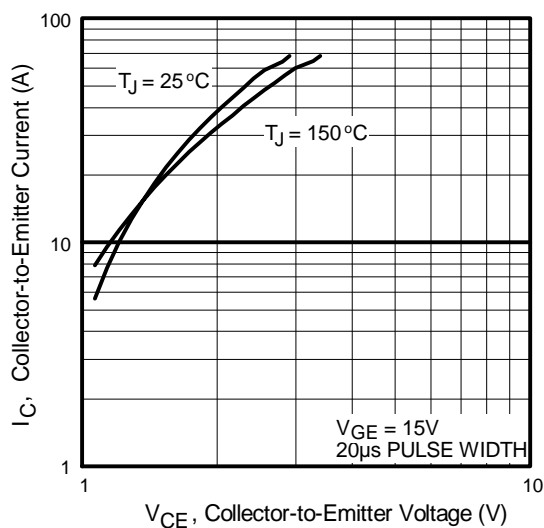


Fig. 2 - Typical Output Characteristics

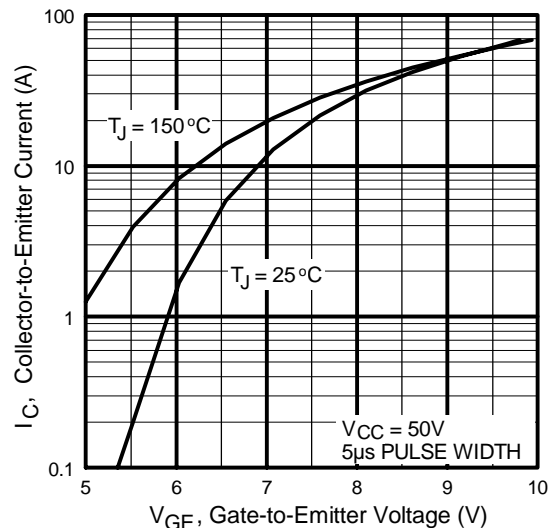


Fig. 3 - Typical Transfer Characteristics

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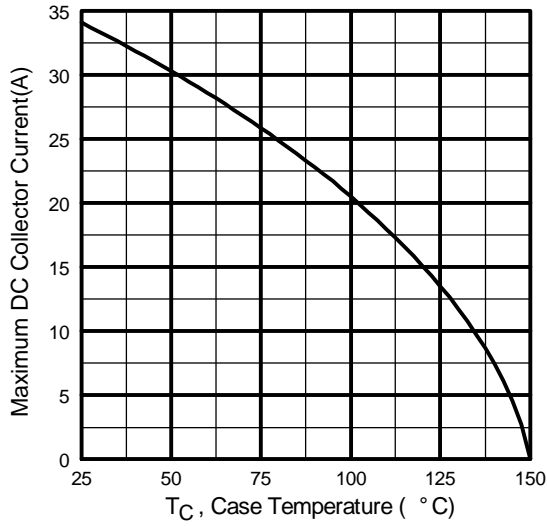


Fig. 4 - Maximum Collector Current vs. Case Temperature

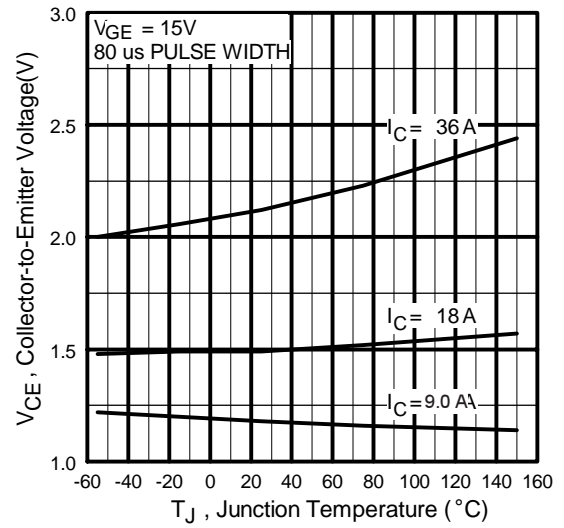


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

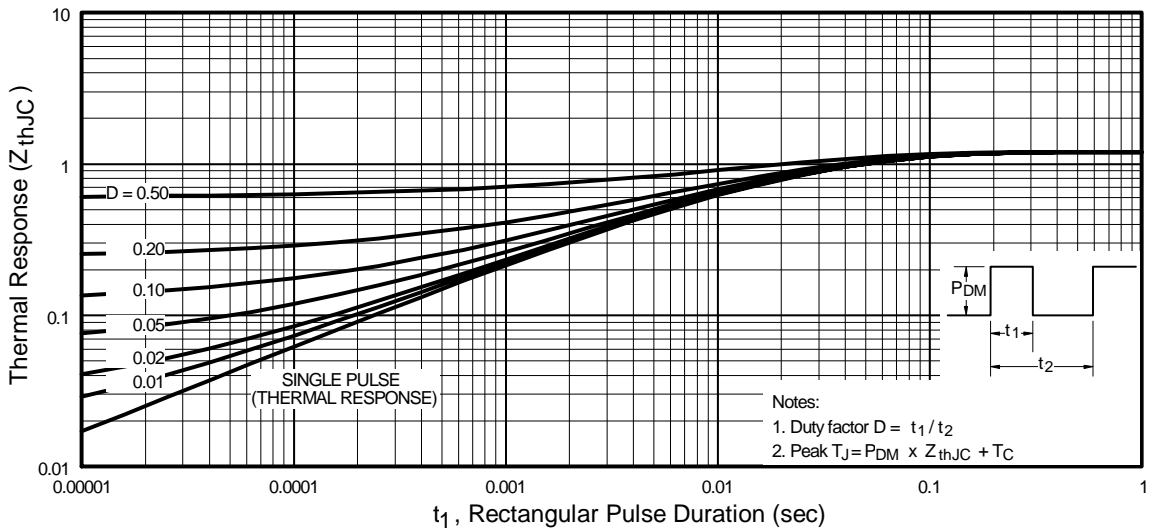


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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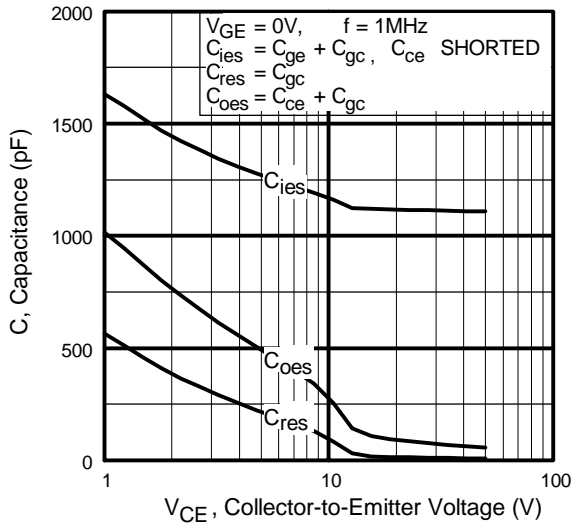


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

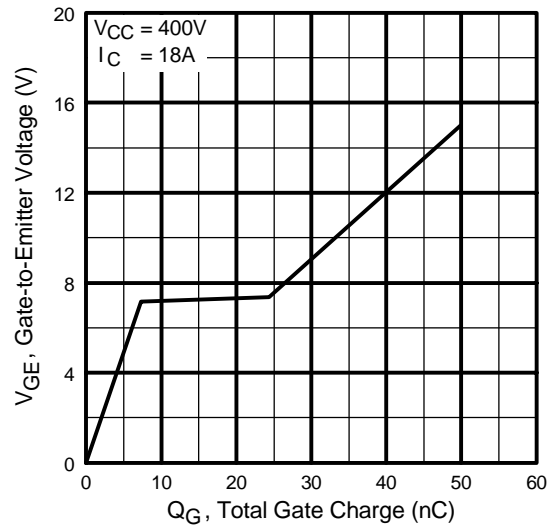


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

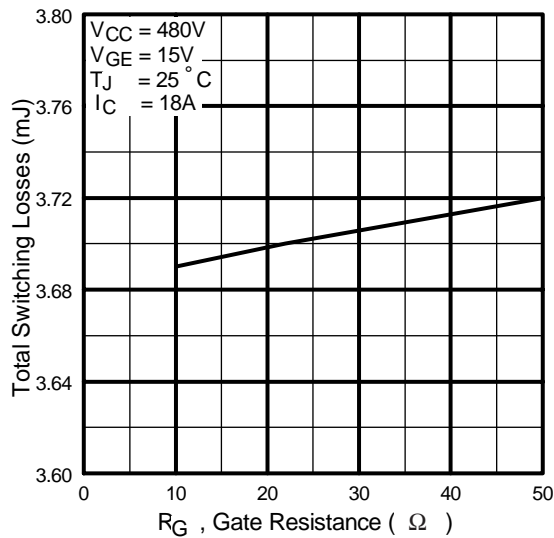


Fig. 9 - Typical Switching Losses vs. Gate Resistance

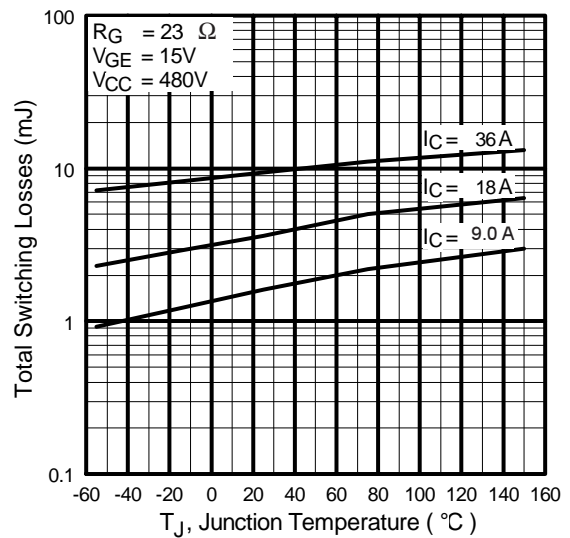


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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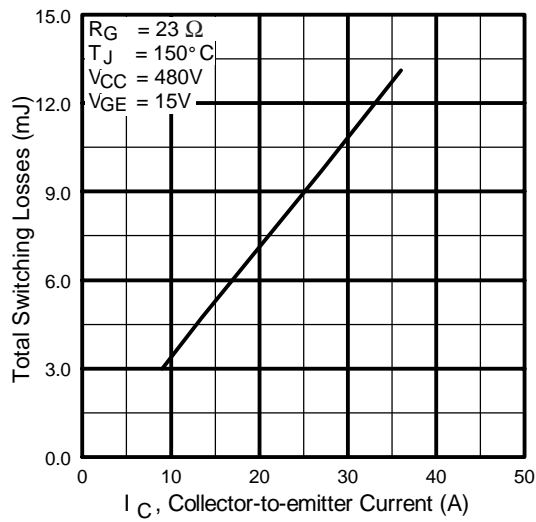


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

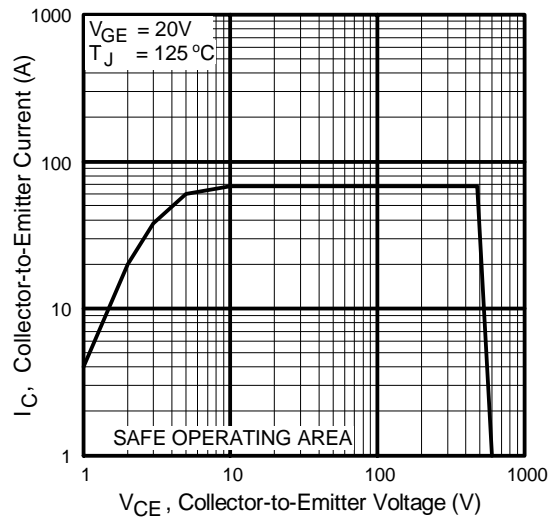
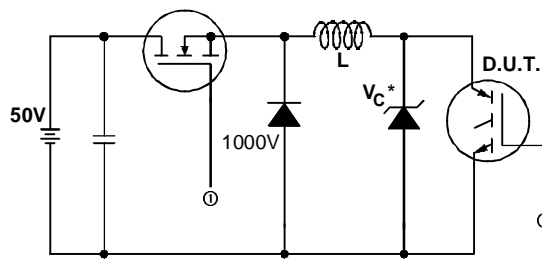


Fig. 12 - Turn-Off SOA



* Driver same type as D.U.T.; $V_c = 80\%$ of $V_{ce(max)}$
* Note: Due to the 50V power supply, pulse width and inductor will increase to obtain rated I_d .

Fig. 13a - Clamped Inductive Load Test Circuit

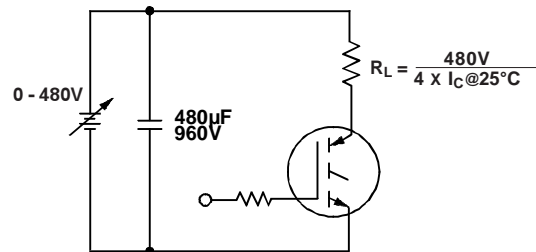


Fig. 13b - Pulsed Collector Current Test Circuit

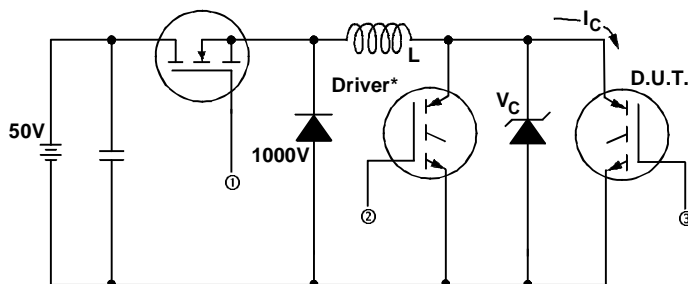


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., $V_C = 480V$

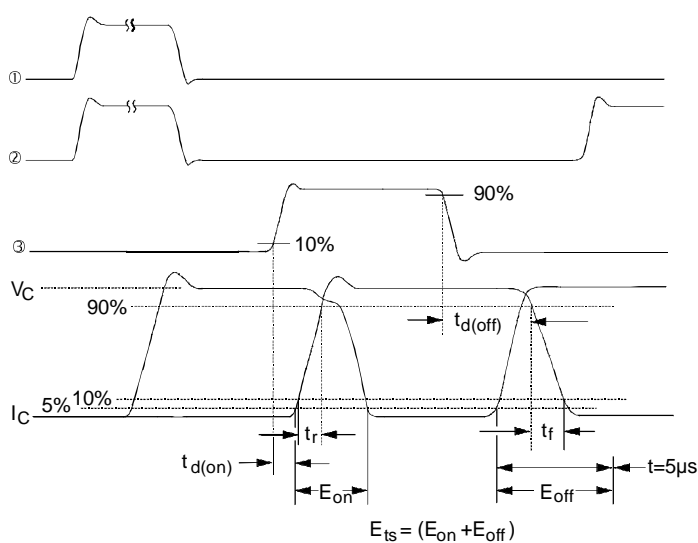


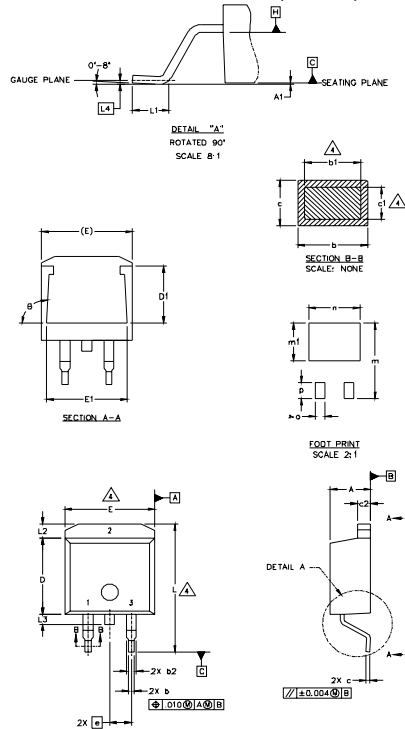
Fig. 14b - Switching Loss Waveforms

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D²Pak Package Outline

Dimensions are shown in millimeters (inches)



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	4
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	
b2	1.14	1.40	.045	.055	4
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	3
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
theta	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

DIODES

- 1.- ANODE *
- 2.- CATHODE
- 3.- ANODE

* PART DEPENDENT.

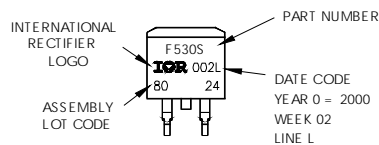
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

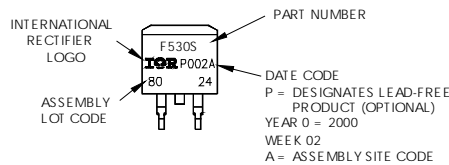
D²Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH
LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line
position indicates "Lead-Free"

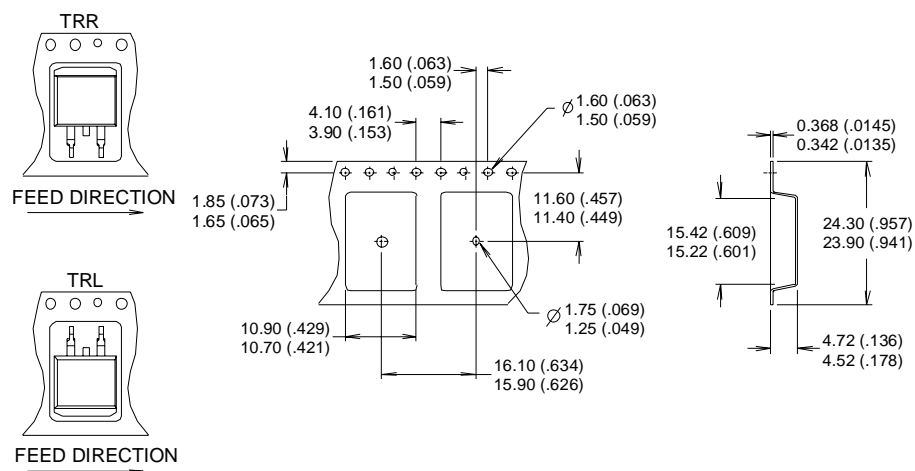


OR



D²Pak Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. COMFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 - ③ DIMENSION MEASURED @ HUB.
 - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the industrial market.
 Qualification Standards can be found on IR's Web site.

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>